



IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

JP 2823

PATENT APPLICATION

Robert Alan Hamm
Rose Fasano Kopf
Robert William Ryan
Alaric Tate
Yu-Chi Wang

CASE 12-14-9-7-5

Serial No. 09/433204 Group Art Unit 2823

Filed November 4, 1999

Examiner T. Dang

Title A Method Of Fabricating A Heterojunction Bipolar Transistor

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

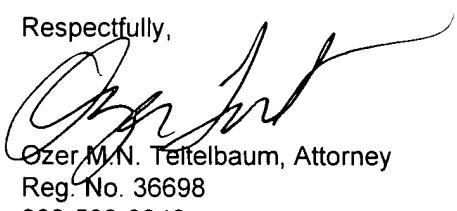
SIR:

Enclosed is an amendment in the above-identified application.

NO ADDITIONAL FEE REQUIRED

In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or to credit Deposit Account No. 12-2325 as required to correct the error.

Respectfully,

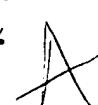


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Date: 6/6/01

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Serial No. 09/433204



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Patent Application

Inventor(s):

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Yu-Chi Wang

Case: 12-14-9-7-5

Serial No.: 09/433,204

Group Art Unit: 2823

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Title: A METHOD OF FABRICATING A HETEROJUNCTION
BIPOLAR TRANSISTOR

TO BE FILED
RECEIVED
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JULY 16 2001

THE COMMISSIONER OF PATENTS AND TRADEMARKS
WASHINGTON, D.C. 20231

AMENDMENT A

In response to the Examiner Dang's Office Action, please enter the following response.

In the Specification:

On page 1, line 4, please enter the following:

--CROSS-REFERENCE TO RELATED APPLICATIONS

Related subject matter is disclosed in co-pending, commonly assigned, U.S. Patent applications Serial Number 09/396,035, filed on September 15, 1999, entitled "Alignment Techniques For Epitaxial Growth Processes." --